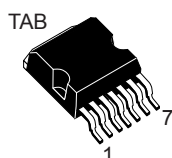
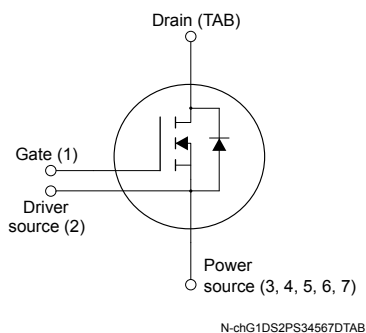


Silicon carbide Power MOSFET 1200 V, 35 mΩ typ., 60 A in an H²PAK-7 package



H²PAK-7



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
SCTH60N120G2-7	1200 V	52 mΩ	60 A

- Very fast and robust intrinsic body diode
- Extremely low gate charge and input capacitance
- Source sensing pin for increased efficiency

Applications

- Switching mode power supply
- DC-DC converters
- Industrial motor control

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 2nd generation SiC MOSFET technology. The device features remarkably low on-resistance per unit area and very good switching performance. The variation of switching loss is almost independent of junction temperature.

Product status link

[SCTH60N120G2-7](#)

Product summary

Order code	SCTH60N120G2-7
Marking	SCT60N120G2V
Package	H ² PAK-7
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1200	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operational values)	-5 to 18	
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	60	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	45	
$I_{DM}^{(1)}$	Drain current (pulsed)	177	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	390	W
T_{stg}	Storage temperature range	-55 to 175	°C
T_J	Operating junction temperature range		°C

1. Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.38	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	1200			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 1200\text{ V}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = -10\text{ to }22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 1\text{ mA}$	1.9	3.0	5.0	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 18\text{ V}$, $I_D = 30\text{ A}$		35	52	m Ω
		$V_{GS} = 18\text{ V}$, $I_D = 30\text{ A}$, $T_J = 175\text{ }^{\circ}\text{C}$		67		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 800\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	1969	-	pF
C_{oss}	Output capacitance		-	113	-	pF
C_{rss}	Reverse transfer capacitance		-	20	-	pF
R_g	Gate input resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1	-	Ω
Q_g	Total gate charge	$V_{DS} = 800\text{ V}$, $V_{GS} = -5\text{ to }18\text{ V}$, $I_D = 30\text{ A}$	-	94	-	nC
Q_{gs}	Gate-source charge		-	22	-	nC
Q_{gd}	Gate-drain charge		-	36	-	nC

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{DD} = 800\text{ V}$, $I_D = 40\text{ A}$	-	617	-	μJ
E_{off}	Turn-off switching energy	$R_G = 4.7\text{ }\Omega$, $V_{GS} = -5\text{ V to }18\text{ V}$	-	188	-	μJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 800\text{ V}$, $I_D = 30\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = -5\text{ to }18\text{ V}$	-	16	-	ns
t_r	Rise time		-	15	-	ns
$t_{d(off)}$	Turn-off delay time		-	32	-	ns
t_f	Fall time		-	14	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 30\text{ A}$, $V_{GS} = 0\text{ V}$	-	3	-	V
t_{rr}	Reverse recovery time	$I_{SD} = 30\text{ A}$, $V_{GS} = 0\text{ V}$, $di/dt = 2000\text{ A}/\mu\text{s}$, $V_{DD} = 800\text{ V}$	-	17	-	ns
Q_{rr}	Reverse recovery charge		-	102	-	nC
I_{RRM}	Reverse recovery current		-	10	-	A

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

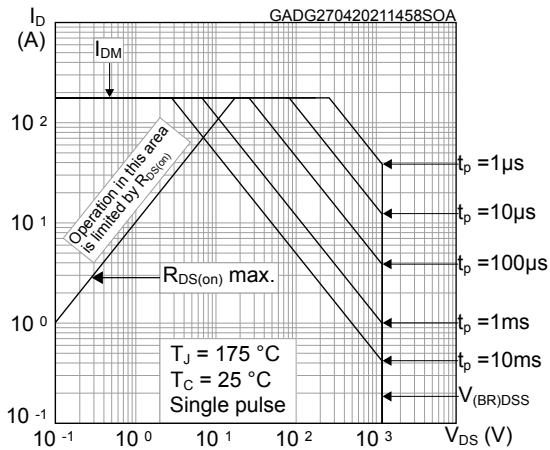


Figure 2. Maximum transient thermal impedance

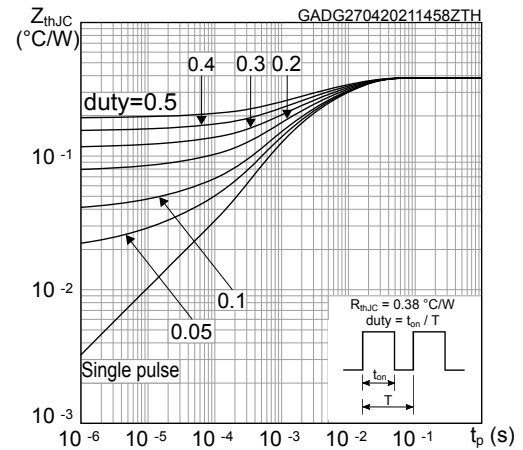


Figure 3. Typical output characteristics ($T_J = 25\text{ °C}$)

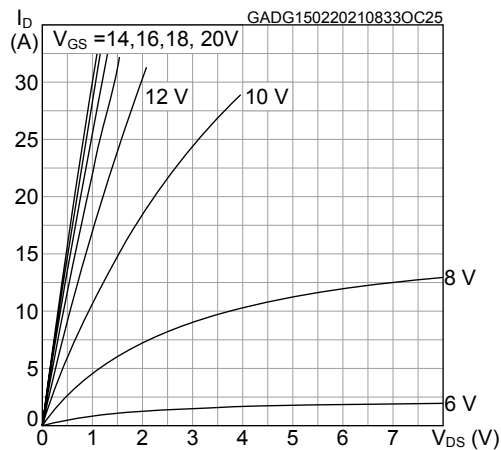


Figure 4. Typical output characteristics ($T_J = 175\text{ °C}$)

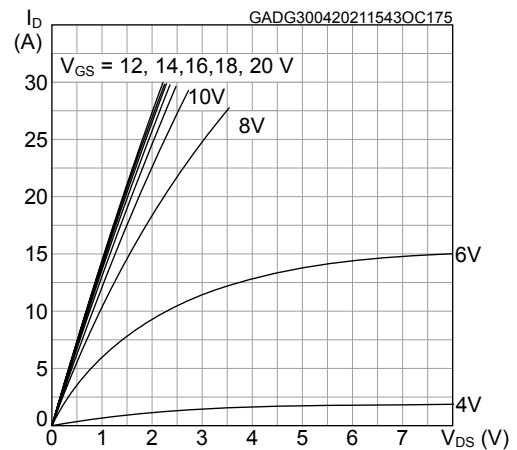


Figure 5. Typical transfer characteristics

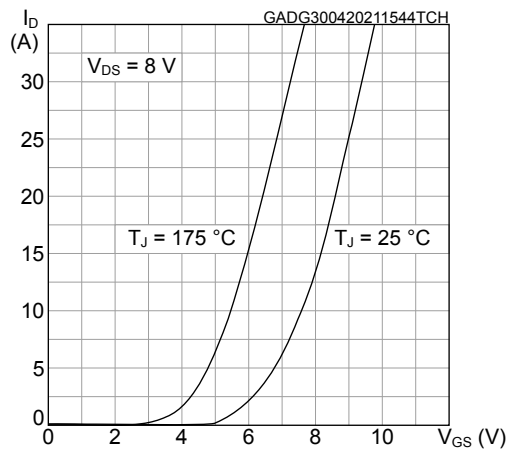


Figure 6. Total power dissipation

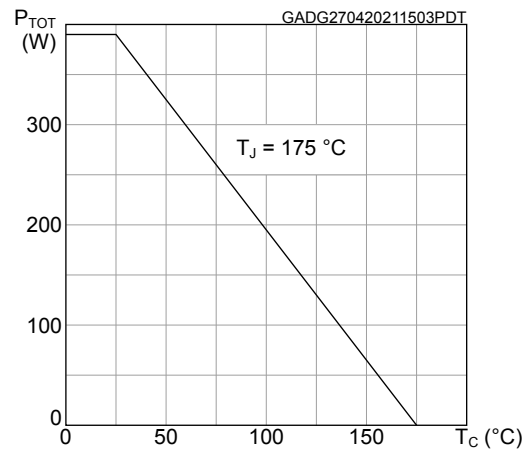


Figure 7. Typical gate charge characteristics

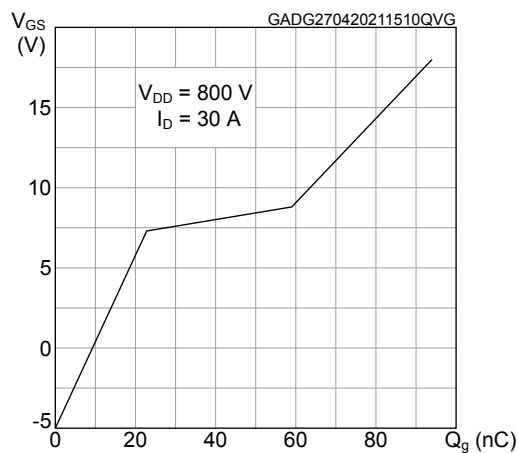


Figure 8. Typical capacitance characteristics

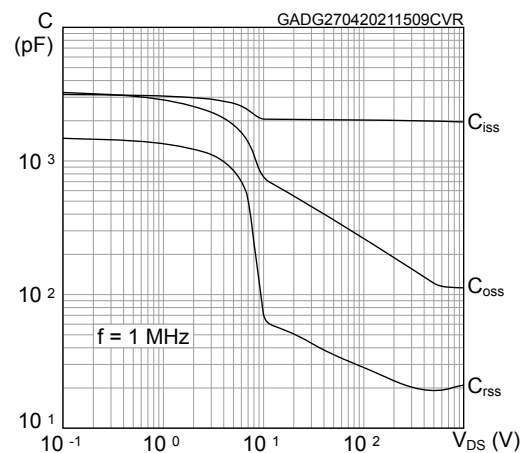


Figure 9. Typical switching energy vs drain current

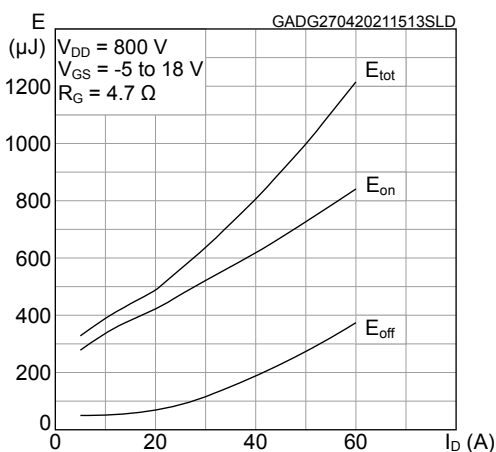


Figure 10. Typical switching energy vs temperature

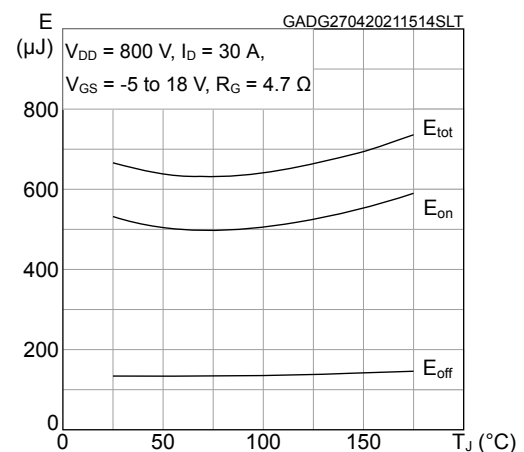


Figure 11. Typical switching energy vs gate resistance

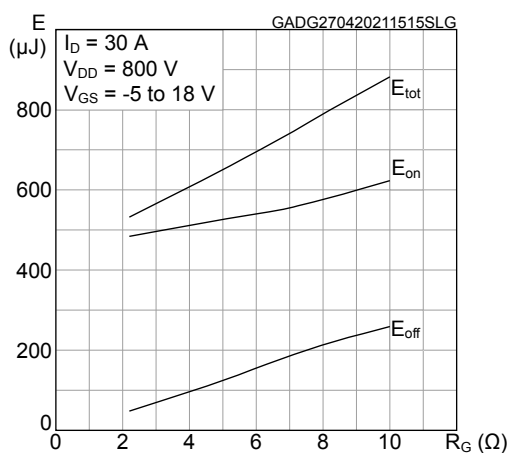


Figure 12. Normalized gate threshold vs temperature

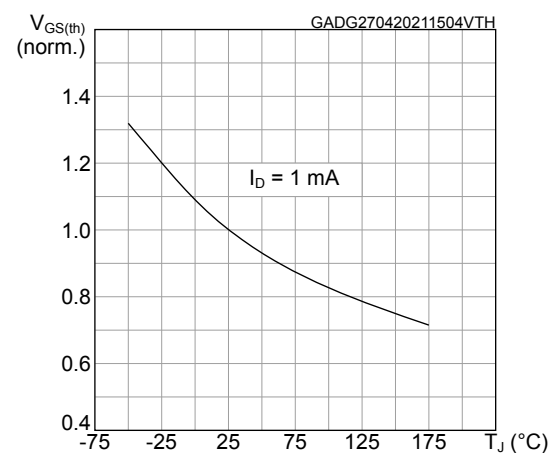


Figure 13. Normalized breakdown voltage vs temperature

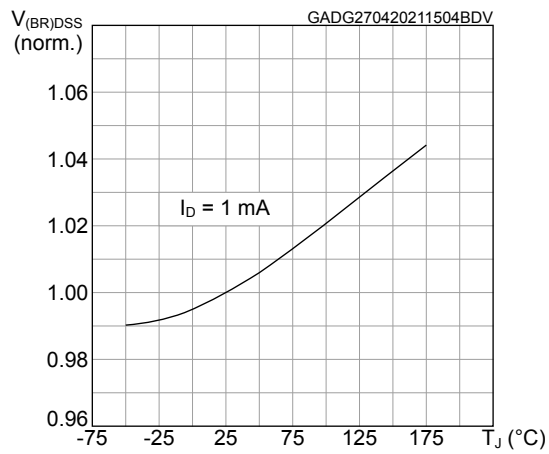


Figure 14. Normalized on-resistance vs temperature

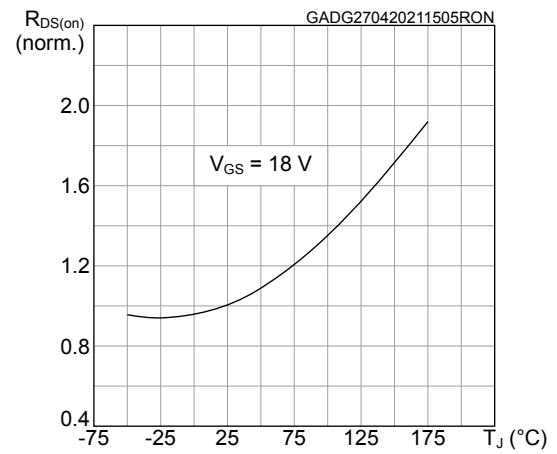


Figure 15. Typical reverse conduction characteristics (TJ = 25 °C)

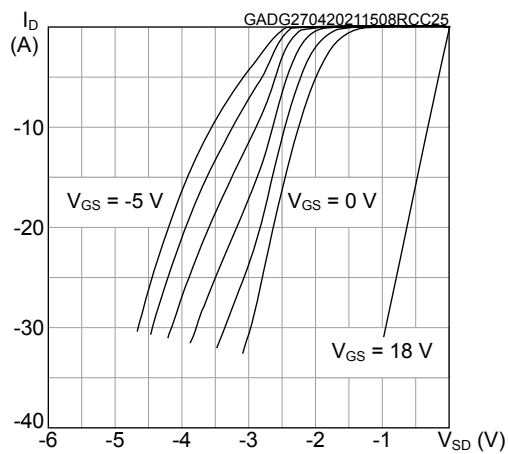
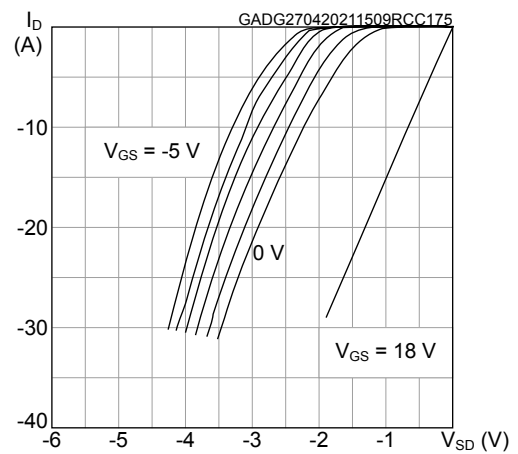


Figure 16. Typical reverse conduction characteristics (TJ = 175 °C)

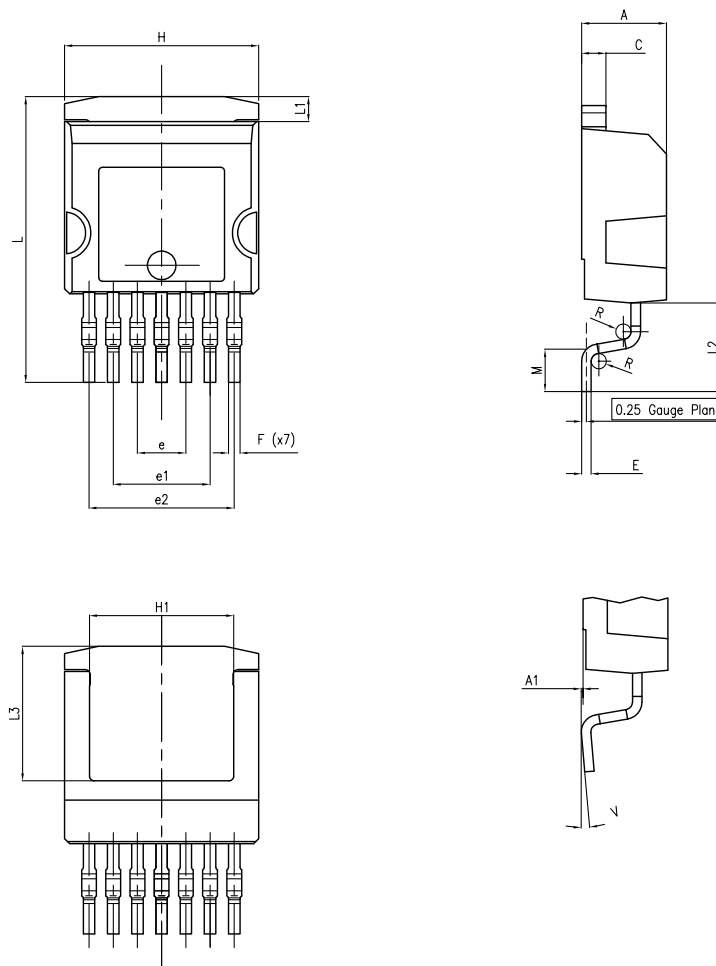


3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 H²PAK-7 package information

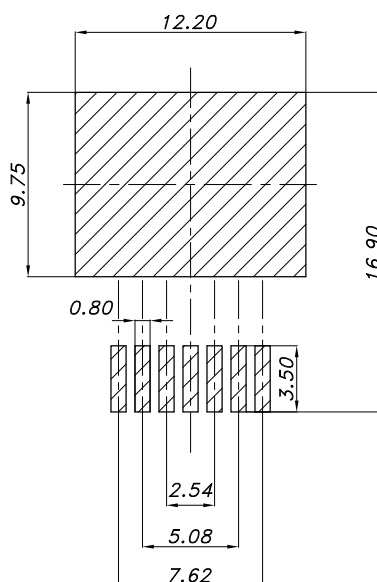
Figure 17. H²PAK-7 package outline



DM00249216_4

Table 8. H²PAK-7 package mechanical data

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	7.60
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

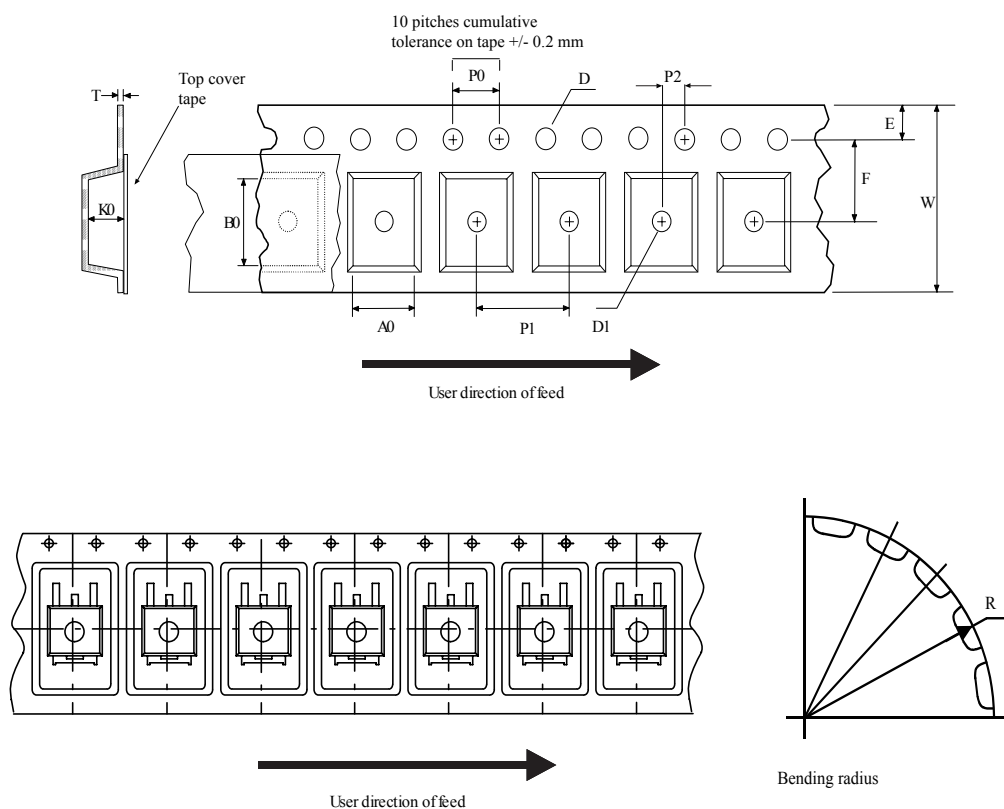
Figure 18. H²PAK-7 recommended footprint


footprint_DM00249216_4

Note: Dimensions are in mm.

3.2 Packing information

Figure 19. Tape outline



AM08852v2

Figure 20. Reel outline

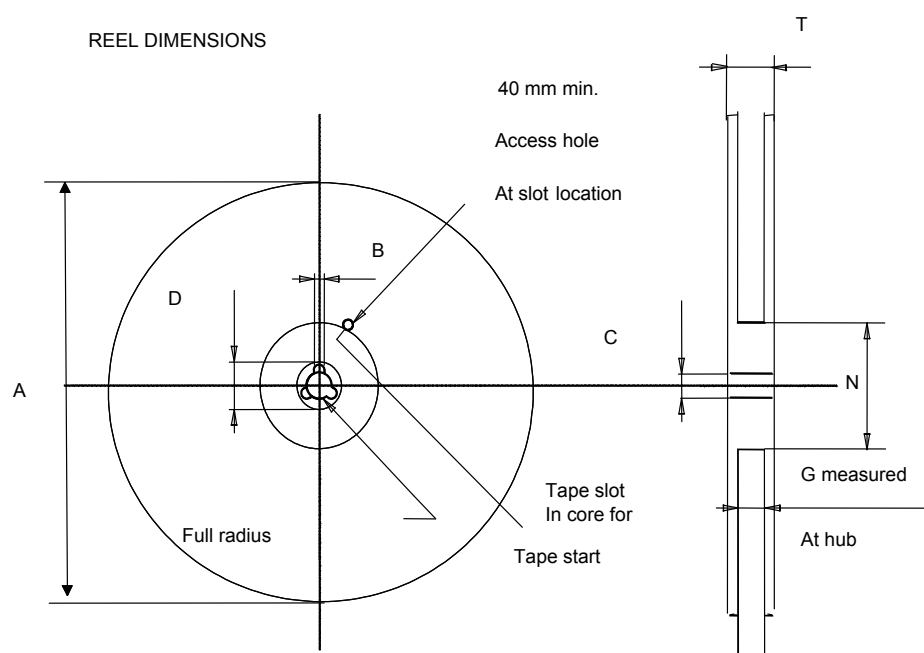


Table 9. Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. Document revision history

Date	Version	Changes
03-May-2021	1	First release.
25-May-2021	2	Modified Table 3. On/off states . Removed test circuits section. Minor text changes.

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